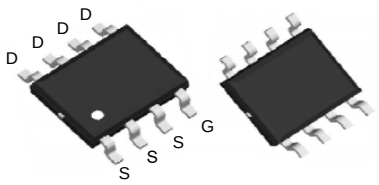
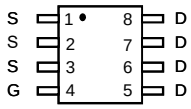
Features

- -100V, -5A
  $R_{DS(ON)}$ < 350mΩ @ V_{GS} = -10V
  $R_{DS(ON)}$ < 400mΩ @ V_{GS} = -4.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free

SOP-8

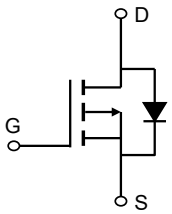


Top View



Applications

- Load Switch
- PWM Application
- Power Management



Absolute Maximum Ratings (@ T_J = 25°C unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		-100	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_A = 25°C	-5	A
		T_A = 100°C	-3	A
I_{DM}	Pulsed Drain Current (1)		-12	A
E_{AS}	Single Pulsed Avalanche Energy (2)		20	mJ
P_D	Power Dissipation	T_A = 25°C	1.9	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (3)		66	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = -250μA, V_{GS} = 0V	-100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -100V, V_{GS} = 0V	-	-	-1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = -250μA	-1	-1.8	-2.4	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(4)	V_{GS} = -10V, I_D = -3A	-	302	350	mΩ
		V_{GS} = -4.5V, I_D = -3A	-	333	400	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = -50V, f = 1MHz	-	1007	-	pF
C_{oss}	Output Capacitance		-	32	-	pF
C_{rss}	Reverse Transfer Capacitance		-	20	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to -10V, V_{DS} = -50V, I_D = -2A	-	88	-	nC
Q_{gs}	Gate Source Charge		-	9	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	16.5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = -10V, V_{DD} = -50V, I_D= -2A, R_{GEN} = 3Ω	-	20	-	ns
t_r	Turn-On Rise Time		-	30	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	55	-	ns
t_f	Turn-Off Fall Time		-	35	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-5	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-12	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = -5A	-	-	-1.2	V
trr	Body Diode Reverse Recovery Time	I_F = -5A, di/dt = 100A/us	-	49	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	71	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25°C, V_{DD}=-100V, V_G=-10V, R_G=25ohm, L=0.5mH, I_{AS}=-12A
3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Test Circuit

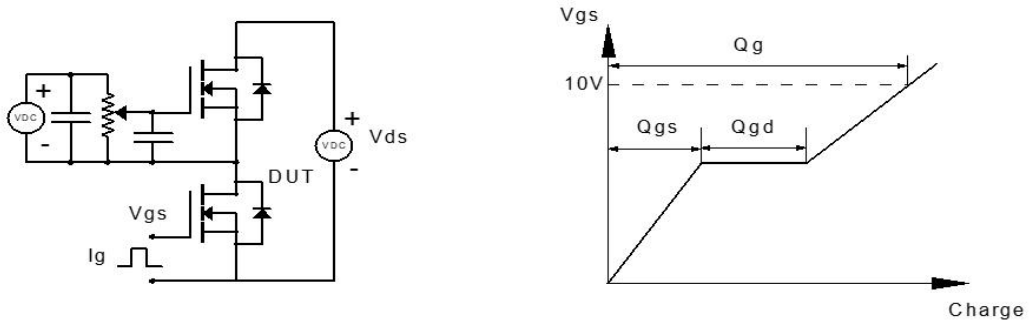


Figure 1: Gate Charge Test Circuit & Waveform

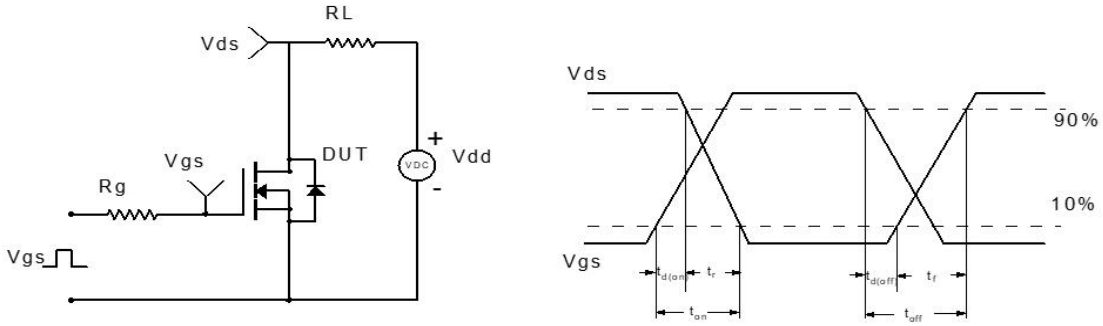


Figure 2: Resistive Switching Test Circuit & Waveform

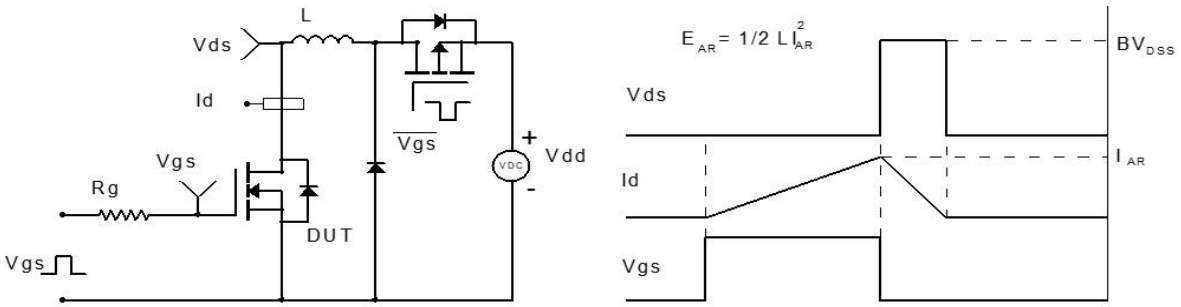


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

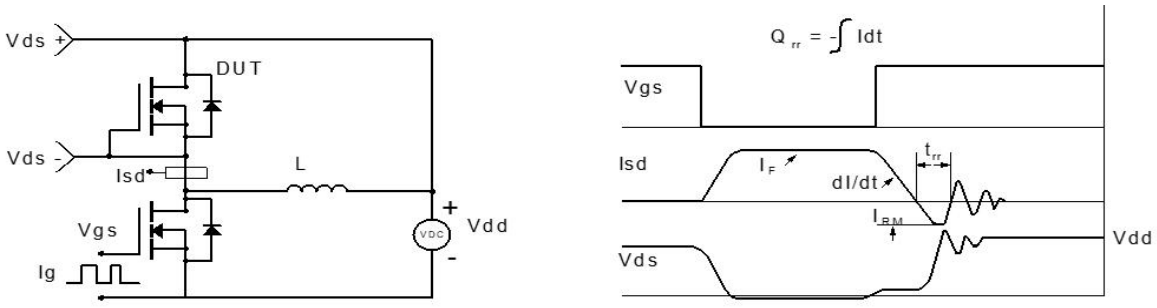
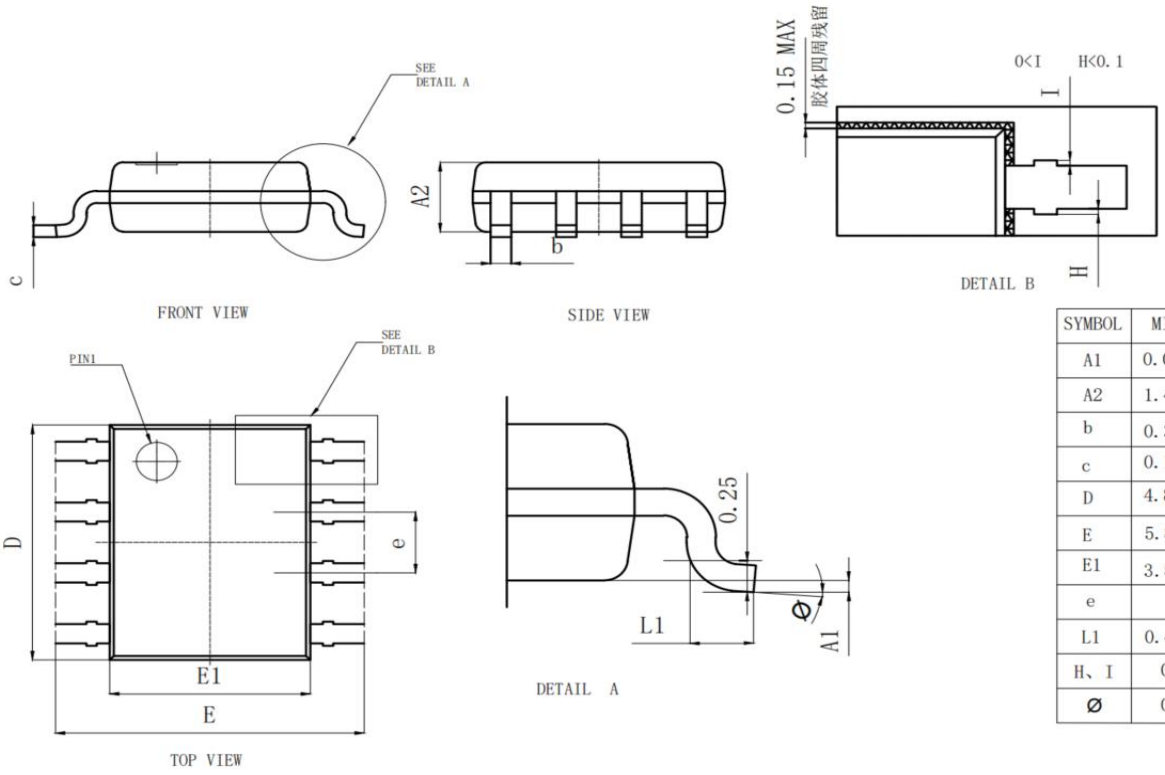


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(SOP-8)



SYMBOL	MIN	NOM	MAX
A1	0.030	0.090	0.150
A2	1.425	1.450	1.475
b	0.300	0.400	0.500
c	0.150	0.200	0.250
D	4.800	5.000	5.200
E	5.800	6.000	6.200
E1	3.800	4.000	4.200
e	1.270BSC		
L1	0.400	0.600	0.800
H、I	0	NA	0.100
Ø	0°	NA	8°